

Customer No.: 31561  
Docket No.: 13531-US-PA  
Application No.: 10/711,498

### REMARKS

#### Present Status of the Application

The Office Action rejected claims 8 and 13-15 under U.S.C. 102(e) as anticipated by Yang (US 7,142,260).

The Office Action rejected claims 8 and 13-15 under U.S.C. 102(e) as anticipated by Yang (US 2005/0190312 A1).

The Office Action rejected claims 9-12 under 35 U.S.C. 103(a) as being unpatentable over Yang (US 7,142,260) or Yang (US 2005/0190312 A1).

Upon entry of the amendments in this response, claims 8-15 remain pending in the present application. More specifically, claim 8 is amended. These amendments are specifically described hereinafter. It is believed that the foregoing amendments add no new matter to the present application.

#### Response To Claim Rejections Under 35 U.S.C. Section 102

*Claims 8 and 13-15 are rejected under U.S.C. 102(e) as anticipated by Yang (US 7,142,260).*

*Claims 8 and 13-15 are rejected under U.S.C. 102(e) as anticipated by Yang (US 2005/0190312 A1).*

Amended claim 8 now recites: "[a] pixel structure for a liquid crystal display panel, comprising:

a first substrate;

a single-type low temperature polysilicon thin film transistor disposed over

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the first substrate, the single-type low temperature polysilicon thin film transistor includes:

- a source and a drain disposed over the first substrate;
  - a channel region disposed between the source and the drain;
  - a gate-insulating layer disposed on the source, the drain and the channel region; and
  - a gate disposed on the gate-insulating layer over the channel region;
- a pixel structure disposed over the first substrate and electrically connected to the single-type low temperature polysilicon thin film transistor;
- a storage capacitor disposed over the first substrate, including a top electrode disposed over the first substrate, an insulating layer disposed on the top electrode and a bottom electrode disposed on the insulating layer, wherein one of the terminals of the storage capacitor is electrically connected to the single-type low temperature polysilicon thin film transistor and the storage capacitor is regarded as a symmetrical capacitor related to the single-type low temperature polysilicon thin film transistor;
- a second substrate disposed over the first substrate;
  - an electrode film disposed on the second substrate;
  - a liquid crystal layer disposed between the first substrate and the second substrate; and
  - a liquid crystal capacitor disposed between the first substrate and the second substrate, wherein one of the terminals of the liquid crystal capacitor and the one of the terminals of the storage capacitor are electrically connected to a same terminal of the

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single-type low temperature polysilicon thin film transistor while the other terminal of the liquid crystal capacitor and the other terminal of the storage capacitor are electrically connected to a common electrode,

**wherein the material of the source and the drain is the same as that of the bottom electrode."**

Yang (US 7,142,260) or Yang (US 2005/0190312 A1) fails to disclose, teach or suggest **the material of the source and the drain is the same as that of the bottom electrode.** In particular, Yang (US 7,142,260) teaches the transparent material of the transparent capacitor electrode 540b is ITO or IZO (Column 7, lines 26-28), which is different from the material of the source/drain doped region 228 formed within the polysilicon layer 222 (Column 3, lines 43-46). Also, Yang (US 2005/0190312 A1) teaches the pixel electrode 270 and the transparent capacitor electrodes 240a and 240b are composed of indium tin oxide (ITO) or indium zinc oxide (IZO) (Paragraph [0038], lines 6-9), which is different from the material of the source/drain doped region 228 formed on both sides of the polysilicon layer 222 (Paragraph [0030], lines 22-24).

However, in the subject matter of amended claim 8, the material of the source and the drain is the same as that of the bottom electrode. Therefore, the subject matter of amended claim 8 has features which are not disclosed by Yang (US 7,142,260) or Yang (US 2005/0190312 A1).

For at least the foregoing reasons, Applicant respectfully submits that Yang (US 7,142,260) or Yang (US 2005/0190312 A1) does not teach each and every element in

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amended claim 8. Independent claim 8 patently define over the prior art reference, and should be allowed.

Claims 13-15 depends on amended claim 8, therefore, claims 13-15 should be also allowed.

**Response To Claim Rejections Under 35 U.S.C. Section 103**

Claims 9-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yang (US 7,142,260) or Yang (US 2005/0190312 A1).

As discussed in the above, amended independent claim 8 should be patentable over Yang (US 7,142,260) or Yang (US 2005/0190312 A1), and should be allowed.

Claims 9-12 depends on amended claim 8, therefore, claim 9-12 should be also allowed.

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**CONCLUSION**

For at least the foregoing reasons, it is believed that the pending claims 8-15 are in proper condition for allowance. If the Examiner believes that a telephone conference would expedite the examination of the above-identified patent application, the Examiner is invited to call the undersigned.

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Respectfully submitted,

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